

# Epitaxial Planar NPN Transistor

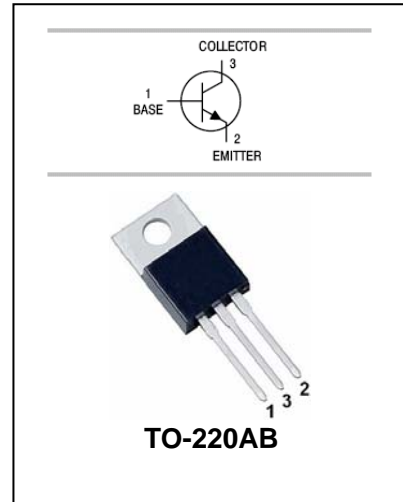
# 2SC4544

## FEATURES

- High Voltage.
- Small Collector Output Capacitance.
- Collector Metal is Fully Covered With Mold Resin.



Lead-free



## MAXIMUM RATING operating temperature range applies unless otherwise specified

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	300	V
$V_{CEO}$	Collector-Emitter Voltage	300	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current	100	mA
$I_B$	Base Current	50	mA
$P_C$	Collector Dissipation	$T_a=25^\circ\text{C}$ 2 $T_c=25^\circ\text{C}$ 8	W
$T_j, T_{stg}$	Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$

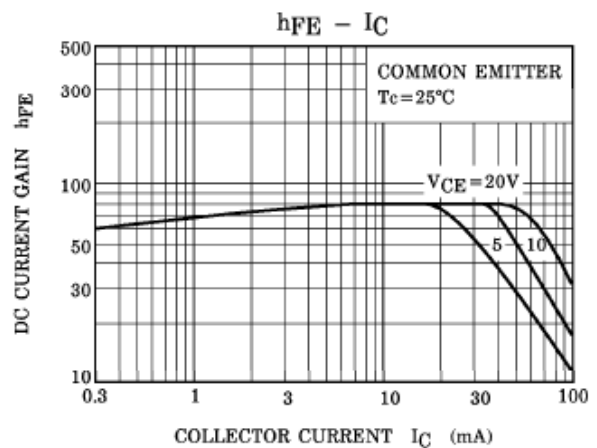
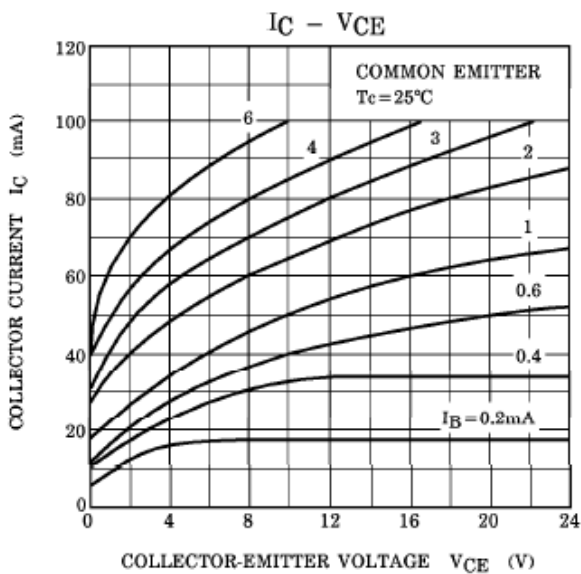
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## ELECTRICAL CHARACTERISTICS Ratings at 25°C ambient temperature unless otherwise specified.

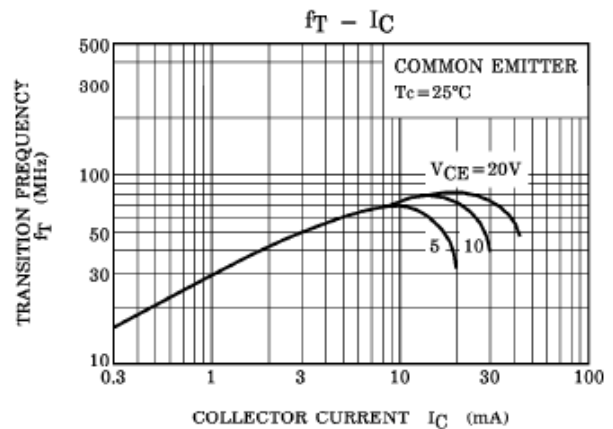
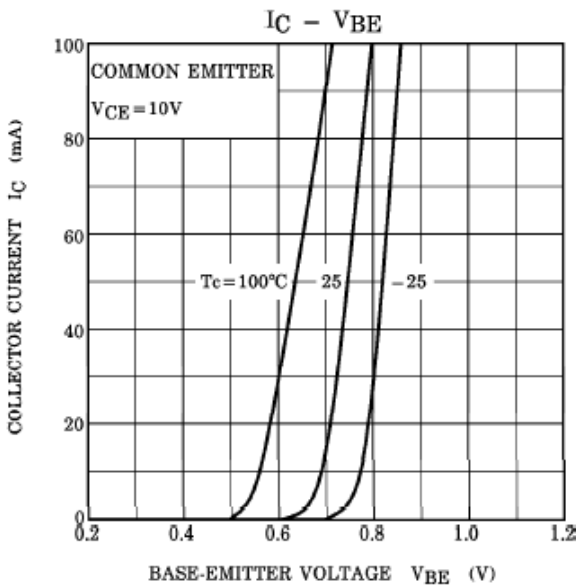
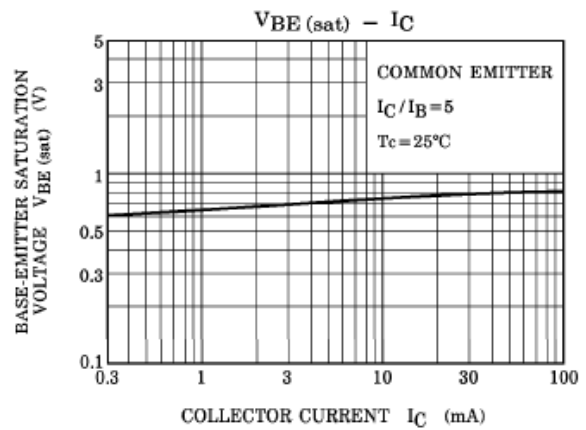
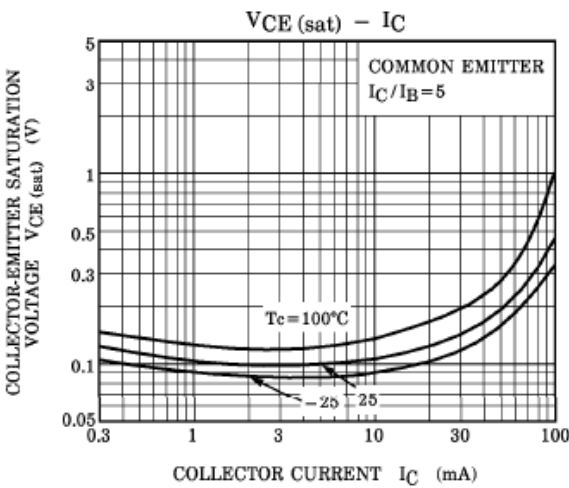
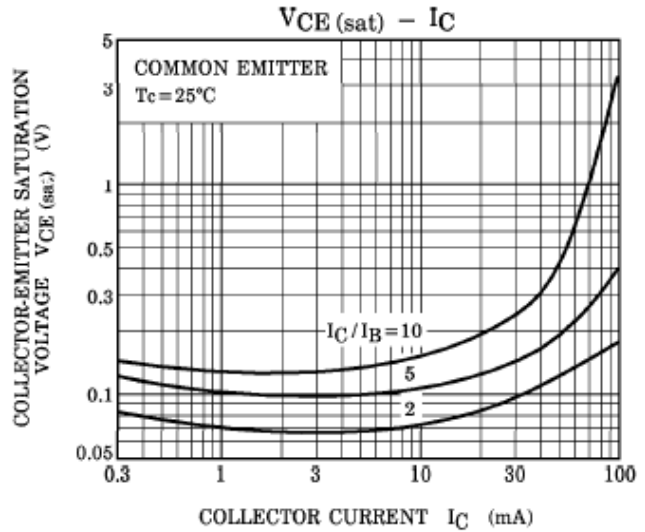
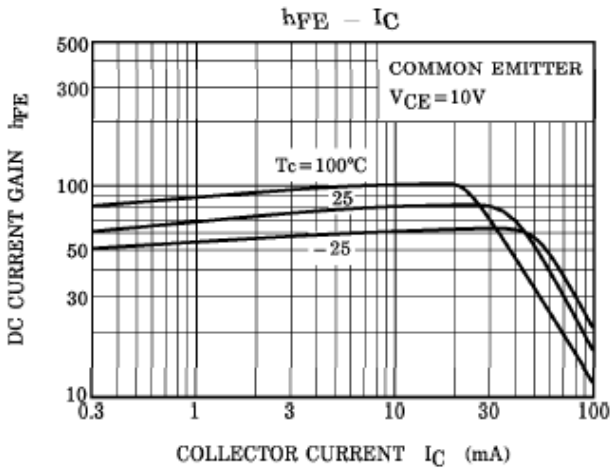
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=240V, I_E=0$			1	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=7V, I_C=0$			1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE}=10V, I_C=4mA$	20			
		$V_{CE}=10V, I_C=20mA$	30		200	
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$			1.0	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=10mA, I_B=1mA$			1.0	V
Transition Frequency	$f_T$	$V_{CE}=10V, I_C=20mA$	50	70		MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=20V, I_E=0,$ $f=1MHz$		3		pF

## TYPICAL CHARACTERISTICS @ $T_a=25^\circ C$ unless otherwise specified



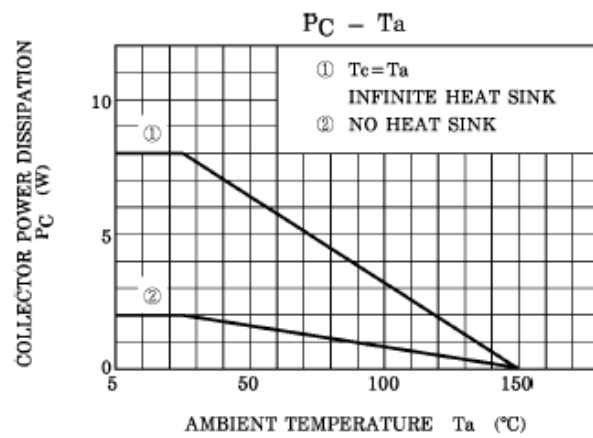
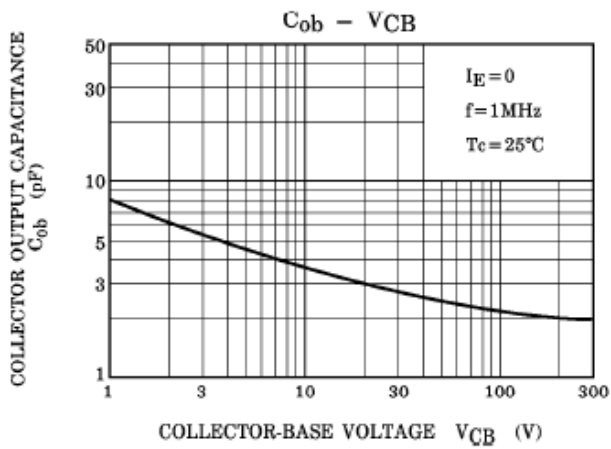
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## PACKAGE OUTLINE

Plastic surface mounted package

TO-220AB

